

Cambridge University Press

978-1-107-40884-5 - Doping Engineering for Device Fabrication: Symposium held
April 18-19, 2006, San Francisco, California, U.S.A.

Edited by B.J. Pawlak, K.S. Jones, S.B. Felch and M. Hane

Index

[More information](#)

AUTHOR INDEX

- Absil, Philippe, 21, 33
 Adachi, Kanna, 149
 Agaiby, Rimoon, 65
 Anwand, Wolfgang, 165
 Aoki, Nobutoshi, 149
 Augendre, Emmanuel, 21, 33, 39,
 77, 203
 Banerjee, Sanjay K., 105
 Beer, C.S., 59
 Bender, Hugo, 191
 Benistant, F., 99
 Benjamin, Mark C., 197
 Bennett, N.S., 59
 Bersani, Massimo, 45, 159
 Bull, Steve J., 65
 Cagnat, Nathalie, 15, 71
 Castrillo, P., 99
 Chattopadhyay, Sanatan, 65
 Clarysse, Trudo, 197
 Collart, Erik J.H., 21, 33, 45
 Colombeau, Benjamin, 45, 59, 99
 Cowern, Nicholas E.B., 21, 33, 45,
 59, 159
 Current, Michael I., 197
 Dao, Thuy, 119
 Delille, Dominique, 27
 De Meyer, Kristin, 39, 77
 Dilliway, G.D., 59
 Duffy, Ray, 33, 119, 203
 Dumont, Benjamin, 15, 27
 Duriez, Blandine, 15
 Edgar, Thomas F., 91
 Eyben, Pierre, 21, 39, 203
 Faifer, Vladimir N., 197
 Falepin, Annelies, 21, 39
 Felch, Susan B., 21, 33, 39, 131,
 137, 191
 Foad, Majeed A., 159
 Gelpey, Jeff, 3
 Gennaro, Salvatore, 159
 Giubertoni, Damiano, 45, 159
 Gonda, V., 173
 Gwilliam, R., 59
 Gwoziecki, Romain, 15
 Hamilton, Justin J., 45, 99
 Harper, R., 59
 Harrison, Scott A., 91
 Hillard, Robert J., 197
 Hopstaken, Marco, 71, 119
 Hwang, Gyeong S., 91, 105
 Ishimaru, Kazunari, 149
 Ishiuchi, Hidemi, 149
 Ito, Takayuki, 149
 Itokawa, Hiroshi, 149
 Jacques, Jeannette M., 53
 Jain, Amitabh, 143
 Janssens, Tom, 21, 33, 191
 Jaraiz, M., 99
 Jones, Britta E., 137
 Jones, Kevin S., 53, 131, 137
 Juhel, Marc, 71
 Kah, Max, 45
 Kanoun, Mehdi, 65
 Kim, Yonghyun, 105
 Kirichenko, Taras A., 105
 Kirkby, Karen J., 45, 159
 Kudo, Toshio Joshua, 111
 Laviron, Cyrille, 15, 71
 Law, Mark E., 53
 Lerch, Wilfried, 3
 Leys, Frederik, 197
 Lin, Rong, 197
 Liu, S., 173
 Loo, Roger, 197
 Maas, Geert, 119
 Martin-Bragado, Ignacio, 99, 179
 Mathiot, Daniel, 15, 71
 Matsuo, Koji, 149
 Mayur, Abhilash, 137
 McCoy, Steve, 3

Cambridge University Press

978-1-107-40884-5 - Doping Engineering for Device Fabrication: Symposium held
April 18-19, 2006, San Francisco, California, U.S.A.

Edited by B.J. Pawlak, K.S. Jones, S.B. Felch and M. Hane

Index

[More information](#)

- | | |
|--|--|
| McMahon, Richard A., 165 | Schreutelkamp, Robert, 21, 33, 39 |
| McNally, P.J., 59 | Sealy, B.J., 59 |
| Milesi, Frederic, 27 | Seffen, Keith A., 165 |
| Mok, K.R.C., 99 | Severi, Simone, 21, 33, 39, 77, 203 |
| Morin, Pierre, 71 | Sharp, James A., 159 |
| Moroz, Victor, 179 | Singer, Julien, 15 |
| Moussa, Alain, 197 | Skorupa, Wolfgang, 165 |
| | Skotnicki, Thomas, 27 |
| Nanver, L.K., 173 | Smith, A.J., 59 |
| Napolitani, Enrico, 53 | Smith, Mark P., 165 |
| Noda, Taiji, 39, 191 | Souifi, Kader, 27 |
| Nouri, Faran, 137 | Srinivasan, M.P., 99 |
| | |
| Ohuchi, Kazuya, 149 | Tamaoki, Naoki, 149 |
| Olsen, Sarah H., 65 | Tamminga, Yde, 119 |
| O'Neill, Anthony, 65 | Timans, Paul, 3 |
| O'Reilly, L., 59 | Tsujii, Hideji, 149 |
| Oudet, Benjamin, 27 | |
| | Uppal, Suresh, 65 |
| Parihar, Vijay, 39, 131, 137, 191 | |
| Paul, Silke, 3 | van der Tak, Karel, 119 |
| Pawlak, Bartek J., 21, 27, 33, 39, 203 | Vandervorst, Wilfried, 21, 33, 39, 191, 197, 203 |
| Petersen, Dirch H., 197 | Venezia, Vincent, 119 |
| Pinacho, R., 99 | Villanueva, Davy, 71 |
| Pouydebasque, Arnaud, 15, 27 | Vrancken, Christa, 191 |
| | |
| Robertson, Lance S., 53 | Wacquant, François, 71 |
| Roozeboom, Fred, 119 | Wakabayashi, Naoki, 111 |
| Rubin, Leonard M., 53 | Webb, Roger P., 159 |
| Rubio, J.E., 99 | |
| | Yoshinori, Honguh, 149 |
| Salvetti, Frédéric, 15, 71 | |
| Scholtes, T.L.M., 173 | Zeenberg, Daniel E., 131, 137 |

SUBJECT INDEX

- activation analysis, 45, 197, 203
- amorphous, 119, 131
- annealing, 3, 33, 77, 143, 149, 165
- As, 91

- B, 15, 21, 53, 71, 159

- C, 21, 33, 39
- chemical vapor deposition (CVD)
 (deposition), 197

- defects, 99, 137, 173, 179
- devices, 21, 27
- diffusion, 15, 27, 45, 53, 65, 91,
 105, 119, 149, 179, 191
- dopant, 197

- electrical properties, 65, 203
- epitaxy, 77, 111

- F, 39

- Ge, 105

- Hall effect, 59

- ion-
 - implantation, 3, 15, 27, 59, 71,
 143, 173
 - solid interactions, 71

- laser, 143
 - annealing, 39, 77, 111, 131,
 137, 149, 159, 173

- nanoscale, 203

- P, 33, 91

- Sb, 59
- secondary ion mass spectroscopy
 (SIMS), 191
- Si, 3, 45, 99, 105, 111, 119, 131,
 159
- simulation, 53, 65, 99, 165, 179,
 191

- thermal stresses, 165
- transmission electron microscopy
 (TEM), 137